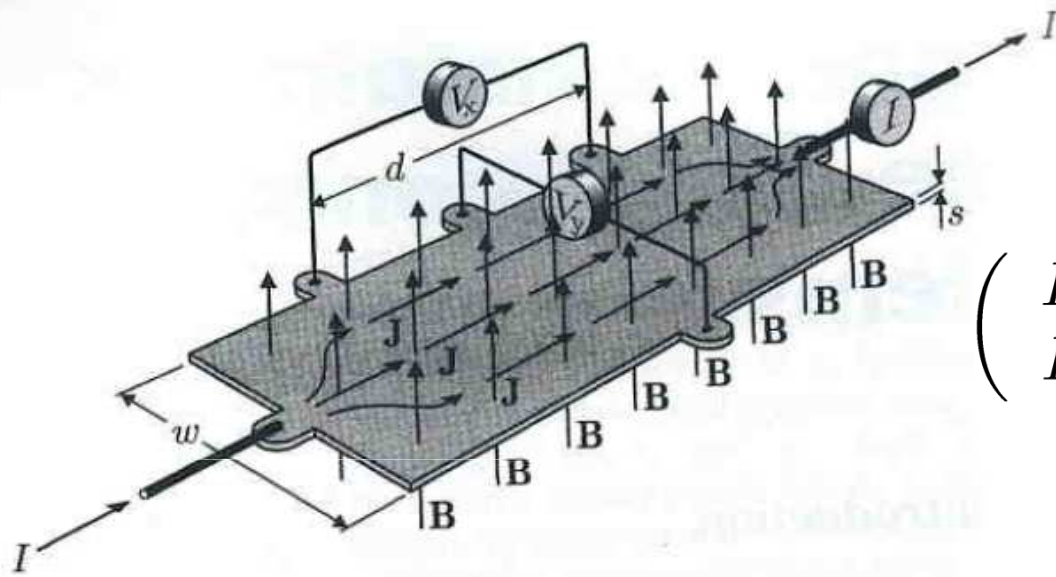


Classical Hall effect: resistivity tensor



$$\mathbf{E} = \rho \cdot \mathbf{J}$$

We have shown that:

$$\begin{pmatrix} E_x \\ E_y \end{pmatrix} = \frac{1}{\sigma_0} \begin{pmatrix} 1 & +\omega_c^e \tau_e \\ -\omega_c^e \tau_e & 1 \end{pmatrix} \begin{pmatrix} J_x \\ J_y \end{pmatrix}$$

$$\rho_{xx} = \rho_0$$

Considering only n-type carriers

$$\mu_e = \frac{e\tau_e}{m_e^*}$$

$$\omega_c^e = \frac{e \cdot B}{m_e^*}$$

Hall Resistivity:

$$\rho_{yx} = -\rho_0 \omega_c^e \tau_e = \frac{B}{(-e)n}$$

Linear in B!

For $J_y = 0$

we get

$$\rho_{xx} = \frac{E_x}{J_x} \quad \rho_{yx} = \frac{E_y}{J_x}$$

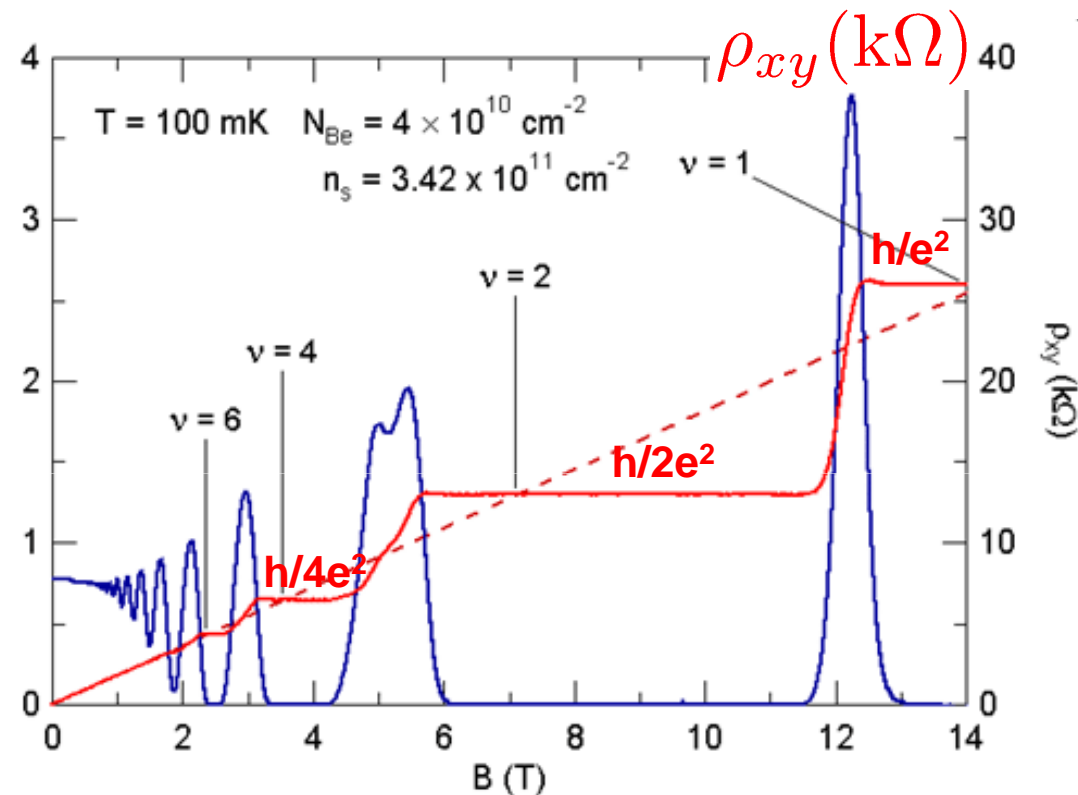
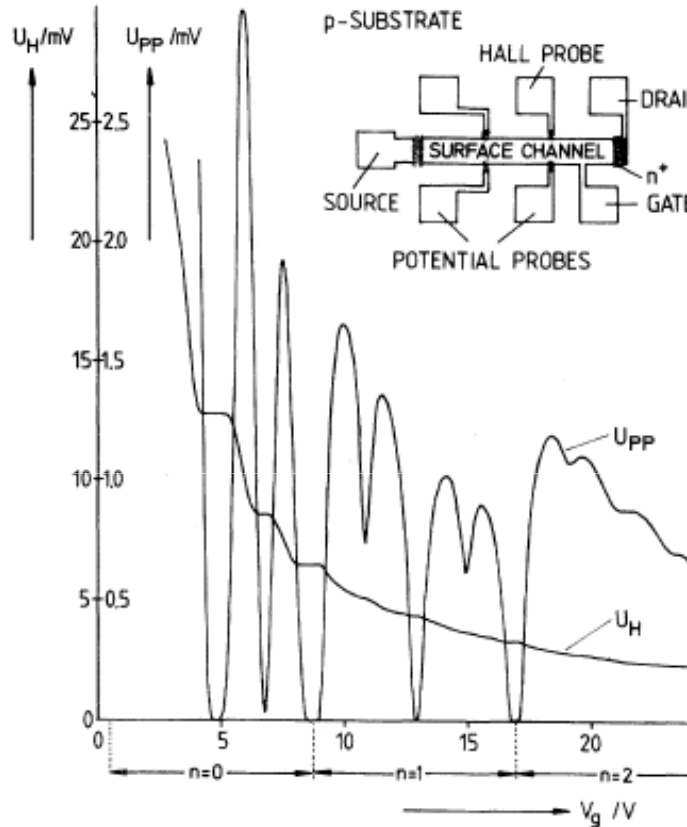
The (integer) quantum Hall effect.



Klaus von Klitzing



1985



Plateaus in ρ_{xy} vs B!

K. v. Klitzing, G. Dorda, M. Pepper,
Phys. Rev. Lett. 45, 494 (1980)

https://www3.physnet.uni-hamburg.de/institute/IAP/Group_N/e/semiconductors/semiconductors_print.html

The (integer) quantum Hall effect.



Klaus von Klitzing



1985

PRL Milestone

Access |

New Method for High-Accuracy Determination of the Fine-Structure Constant Based on Quantized Hall Resistance

K. v. Klitzing, G. Dorda, and M. Pepper

Phys. Rev. Lett. **45**, 494 – Published 11 August 1980

An article within the collection: [Letters from the Past - A PRL Retrospective](#)

Citing Articles (2,782)

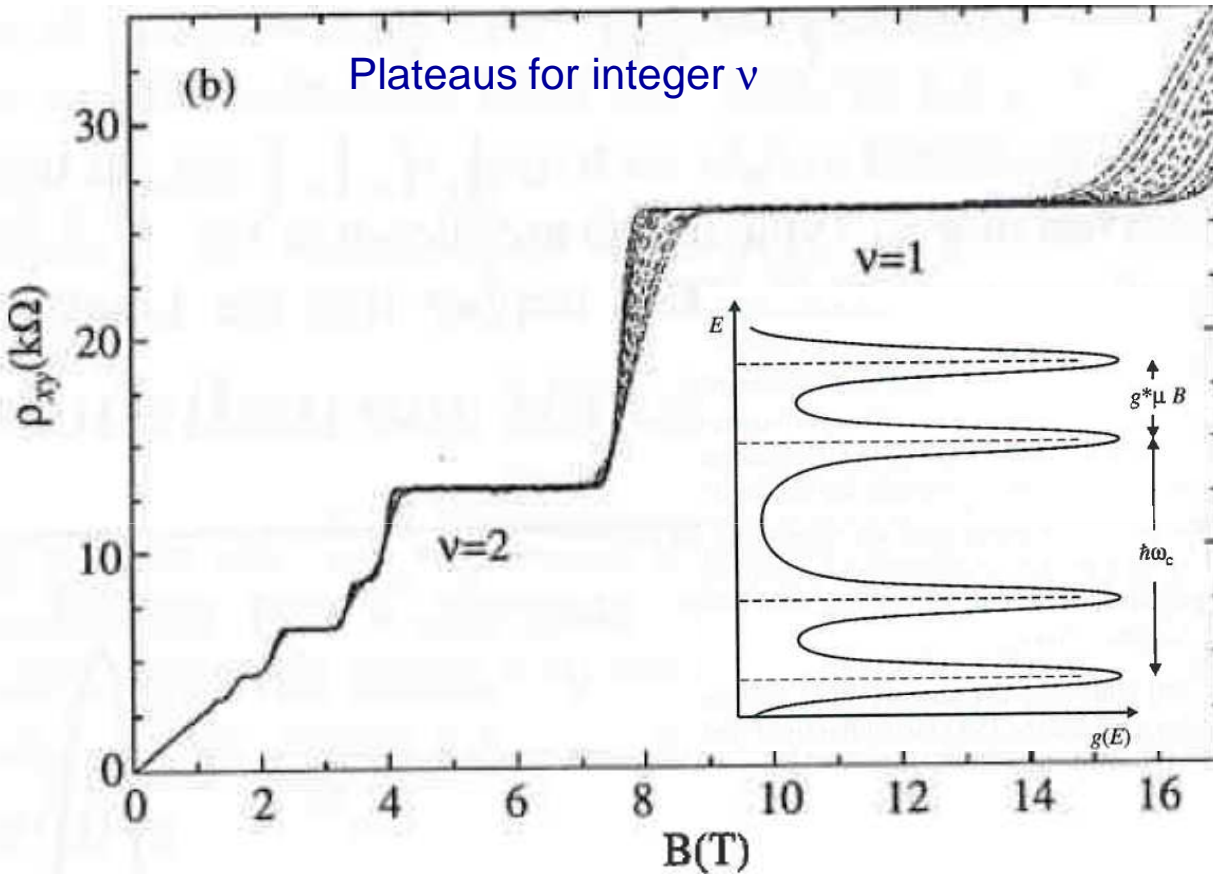
PDF

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Foz do Iguaçu 2015

Quantum Hall effect: resistivity plateaus



Zeeman splitting of Landau levels: one spin per state

$$e = 1,6 \times 10^{-19} \text{ Coulomb}$$

$$\hbar = 6,58212 \times 10^{-16} \text{ eV.s}$$

“Doubly filled” j th Landau level (given density n):

$$n = j_{\max} \frac{2eB}{h}$$

“Filling factor” ν (per spin): $\nu = \frac{nh}{eB}$

Hall Resistivity:

$$\rho_{yx} = \frac{B}{(-e)n} = \frac{1}{\nu} \frac{h}{e^2}$$

Resistivity quantization!

$$\frac{h}{e^2} = ??? \Omega$$

Tarefa 16 (em sala, agora)

The (integer) quantum Hall effect.

Séminaire Poincaré 2 (2004) 1 - 16

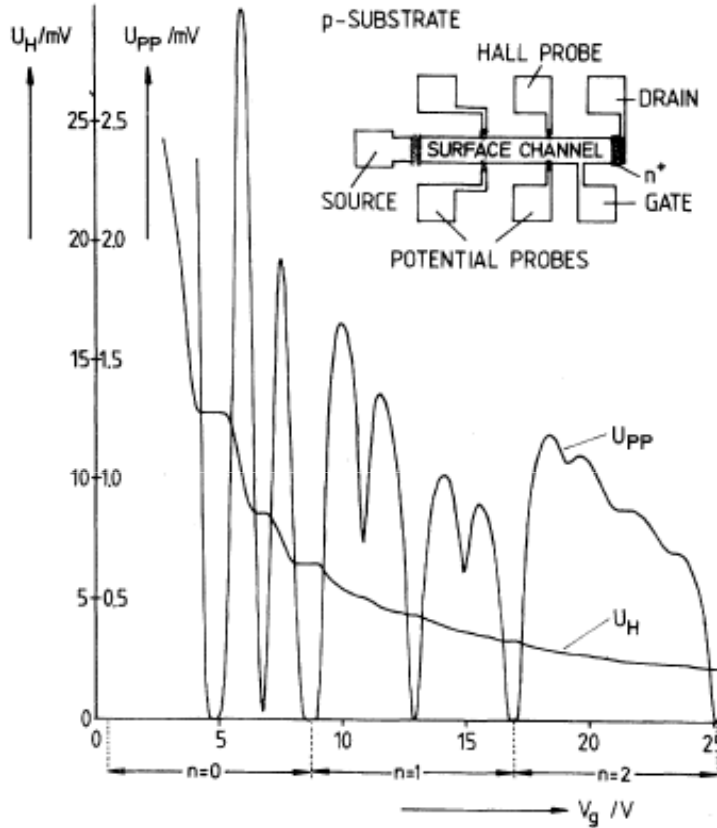


Klaus von Klitzing



1985

K. v. Klitzing, G. Dorda, M. Pepper,
Phys. Rev. Lett. 45, 494 (1980)



Notes 4.5.2.1980

rotating sample holder

pin connections

Josephson

$$E_H = R_H \cdot B \cdot j = \frac{1}{n \cdot e} \cdot B \cdot \frac{I}{b}$$

$$U_H = \frac{B}{n \cdot e} \cdot I$$

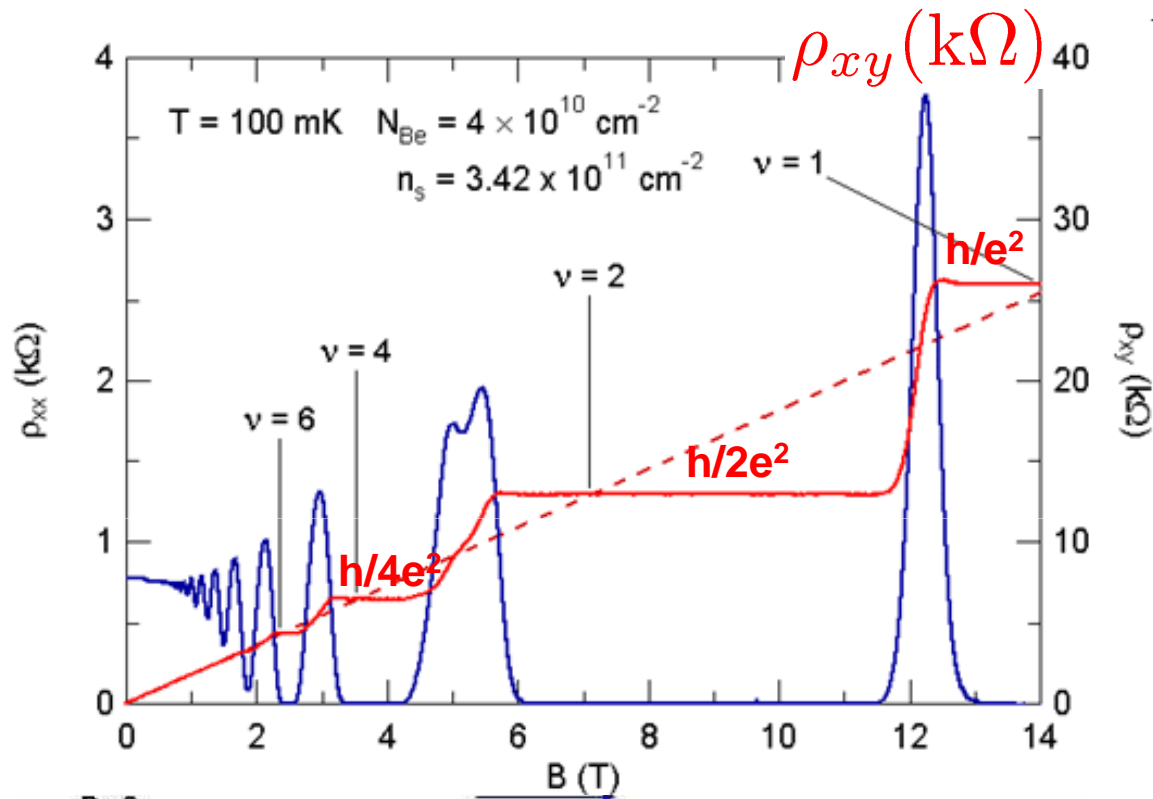
$$U_H = \frac{2\pi\hbar}{e \cdot e \cdot B} \cdot I = \frac{h}{e^2} \cdot I$$

25,76 kΩ
25813

$$N = \frac{eB}{2\pi\hbar} \quad (\nu_s \cdot \nu_v = 1)$$

$$\frac{e^2}{4\pi} \sqrt{\frac{\mu_0}{\epsilon_0}} = \frac{h}{2e^2} \Rightarrow 25813 \text{ } \Omega$$

Quantum Hall effect: resistivity plateaus



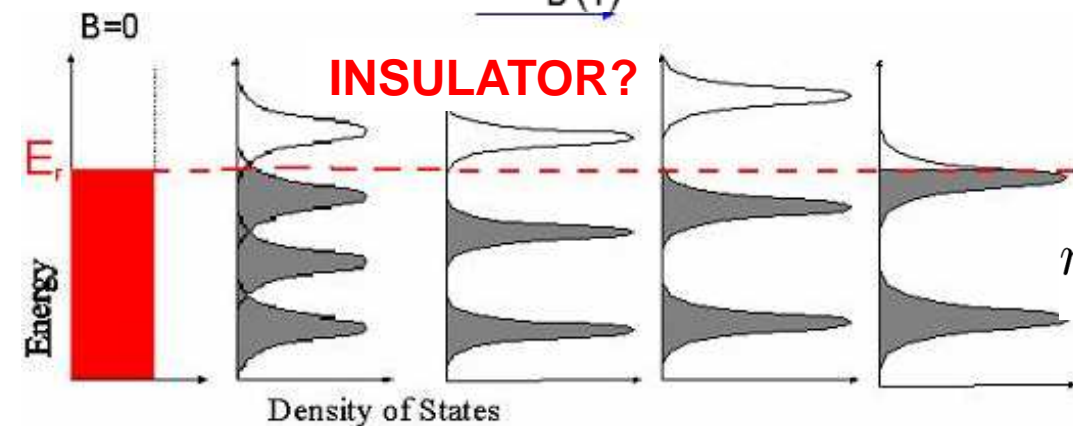
Plateaus in the Hall resistivity for integer ν

$$\rho_{yx} = \frac{1}{\nu} \frac{h}{e^2} \quad \nu = \frac{nh}{eB}$$

Now, the longitudinal resistivity goes to zero!

$$\rho_{xx} = \frac{\sigma_{xx}}{\sigma_{xx}^2 + \sigma_{xy}^2} \approx \frac{\sigma_{xx}}{\sigma_{xy}^2} \rightarrow 0$$

No magnetoresistance for $\omega_c \tau$ large !?!



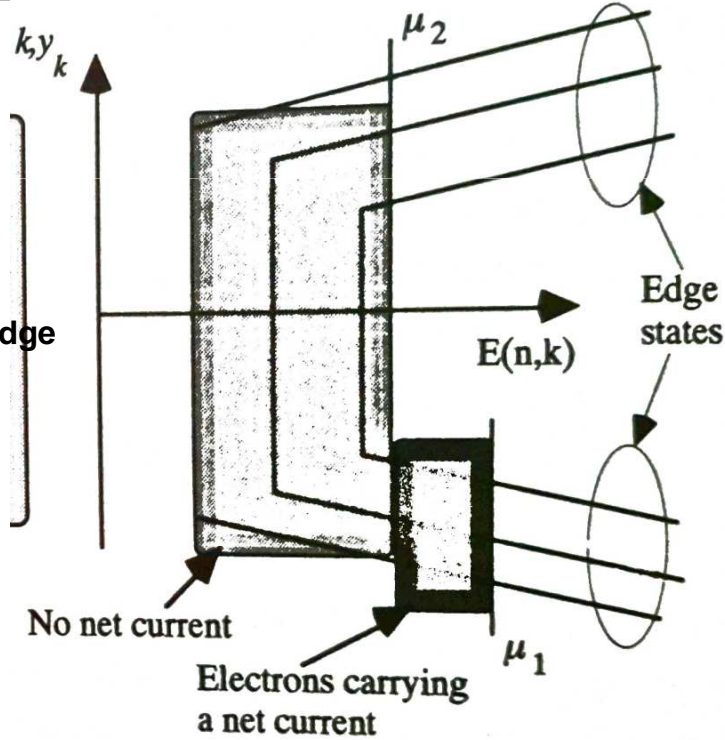
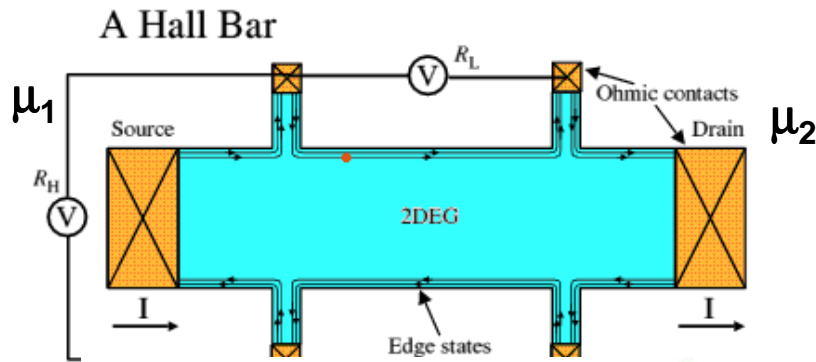
$$n = j_{\max} \frac{2eB}{h}$$

Landau edge states

D.R. Leadley, Warwick University 1997

<http://www.sp.phy.cam.ac.uk/research/fundamentals-of-low-dimensional-semiconductor-systems/lowD>

Datta, *Electronic Transport in Mesoscopic Systems*, Cambridge Press



Potential $V(y)$: edge states

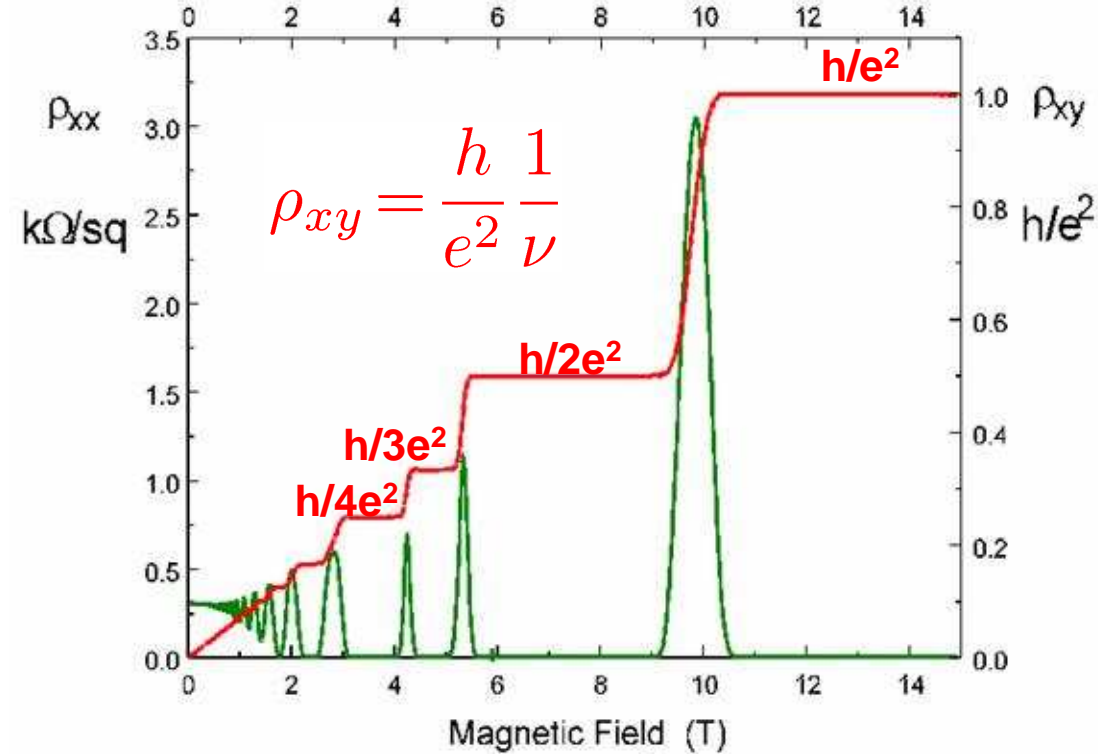


Fig 4: Red is the graph of hall resistance in units of h/e^2 versus magnetic field in tesla.

